

General Purpose Transistors

PNP Silicon

BC807-16L, BC807-25L, BC807-40L

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

COLLECTOR 3 BASE 2 EMITTER



SOT-23 CASE 318 STYLE 6

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	-45	V
Collector - Base Voltage	V _{CBO}	-50	V
Emitter – Base Voltage	V _{EBO}	-6.0	V
Collector Current – Continuous	I _C	-500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	436	°C/W
Total Device Dissipation Alumina Substrate, (Note 1) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. FR–4 Board, 1 oz. Cu, 100mm².
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in 99.5% alumina.

MARKING DIAGRAM



5xx = Device Code xx = A1, B1, or C M = Date Code* • = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic			Тур	Max	Unit
	V _{(BR)CEO}	-45	_	_	V
	V _(BR) CES	-50	_	_	V
	V _{(BR)EBO}	-6.0	-	_	V
	Ісво	_ _	- -	-100 -5.0	nA μA
07-16, SBC80-16L 7-25, SBC807-25L 7-40, SBC807-40L	h _{FE}	100 160 250 40	- - -	250 400 600	-
	V _{CE(sat)}	_	-	-0.7	V
	V _{BE(on)}	_	-	-1.2	V
		-	-	-	
	f _T	100	_	_	MHz
	C _{obo}	_	10	-	pF
	'-25, SBC807-25L	V _{(BR)CES} V _{(BR)EBO} ICBO ICBO NFE VCE(sat) VBE(on)	V _{(BR)CEO} -45 V _{(BR)CES} -50 V _{(BR)EBO} -6.0 I _{CBO} - - - - - - - - - - - - -	V(BR)CEO	V(BR)CEO

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Specific Marking	Package	Shipping [†]	
BC807-16LT1G	504	SOT-23 (Pb-Free)	3000 / Tape & Reel	
SBC807-16LT1G*	5A1			
BC807-16LT3G	5A1		10.000 / Tana % Daal	
SBC807-16LT3G*	5A1		10,000 / Tape & Reel	
BC807-25LT1G	5B1		3000 / Tape & Reel	
SBC807-25LT1G*	351			
BC807-25LT3G	5B1		10,000 / Tape & Reel	
SBC807-25LT3G*	351		10,000 / Tape & Neel	
BC807-40LT1G	5C		2000 / Tono & Dool	
SBC807-40LT1G*	50		3000 / Tape & Reel	
BC807-40LT3G	5C		10 000 / Tana & Baal	
SBC807-40LT3G*	50		10,000 / Tape & Reel	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

TYPICAL CHARACTERISTICS - BC807-16LT1

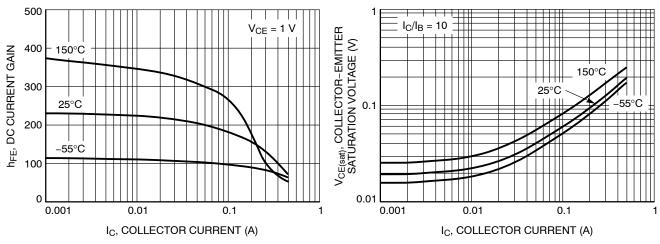


Figure 1. DC Current Gain vs. Collector Current

Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

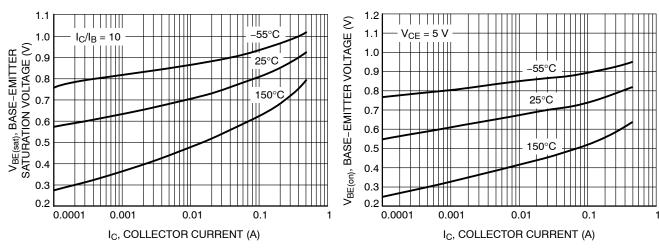


Figure 3. Base Emitter Saturation Voltage vs. Collector Current

Figure 4. Base Emitter Voltage vs. Collector Current

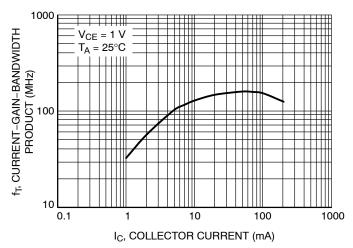


Figure 5. Current Gain Bandwidth Product vs.
Collector Current

TYPICAL CHARACTERISTICS - BC807-16LT1

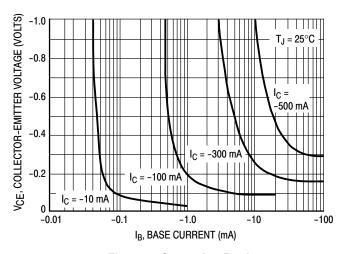


Figure 6. Saturation Region

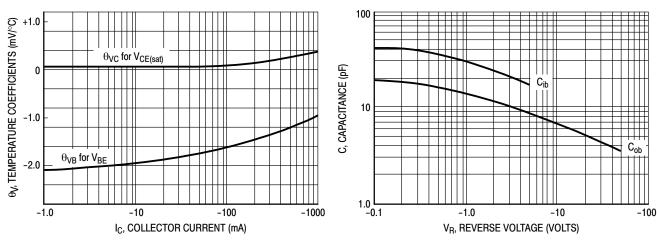


Figure 7. Temperature Coefficients

Figure 8. Capacitances

TYPICAL CHARACTERISTICS - BC807-25LT1

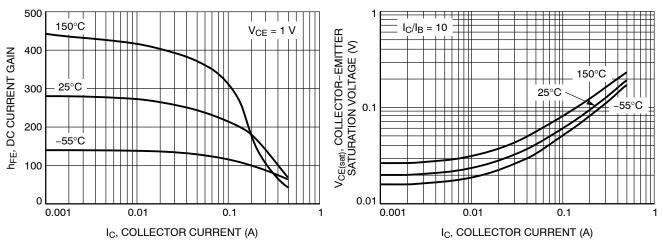


Figure 9. DC Current Gain vs. Collector Current

Figure 10. Collector Emitter Saturation Voltage vs. Collector Current

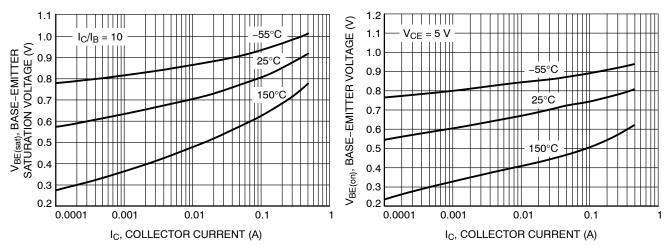


Figure 11. Base Emitter Saturation Voltage vs. Collector Current

Figure 12. Base Emitter Voltage vs. Collector Current

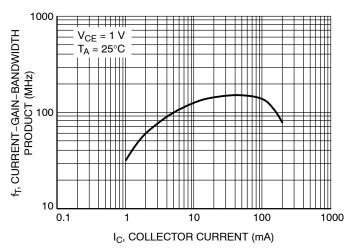


Figure 13. Current Gain Bandwidth Product vs. Collector Current

TYPICAL CHARACTERISTICS - BC807-25LT1

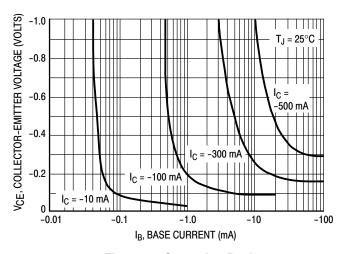


Figure 14. Saturation Region

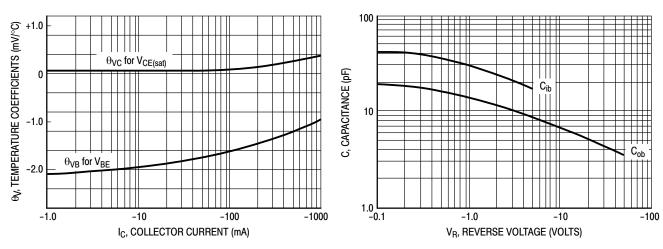


Figure 15. Temperature Coefficients

Figure 16. Capacitances

TYPICAL CHARACTERISTICS - BC807-40LT1

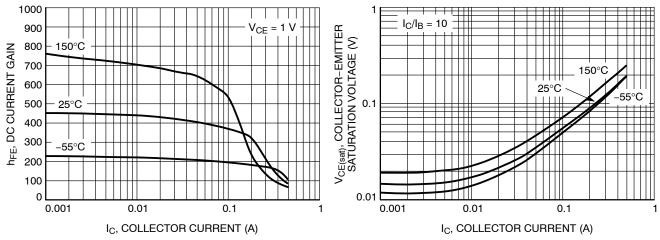


Figure 17. DC Current Gain vs. Collector Current

Figure 18. Collector Emitter Saturation Voltage vs. Collector Current

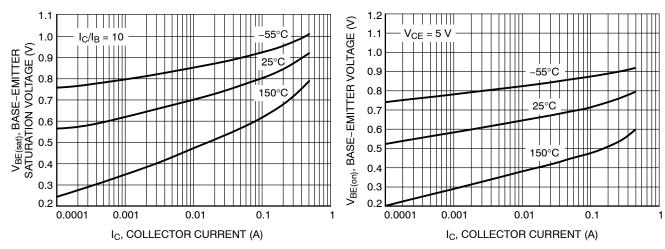


Figure 19. Base Emitter Saturation Voltage vs. Collector Current

Figure 20. Base Emitter Voltage vs. Collector Current

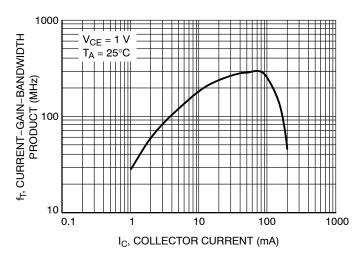


Figure 21. Current Gain Bandwidth Product vs. Collector Current

TYPICAL CHARACTERISTICS - BC807-40LT1

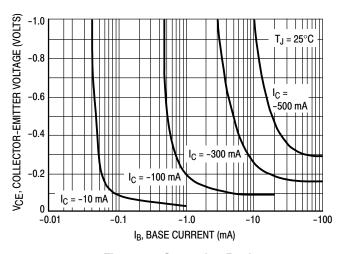


Figure 22. Saturation Region

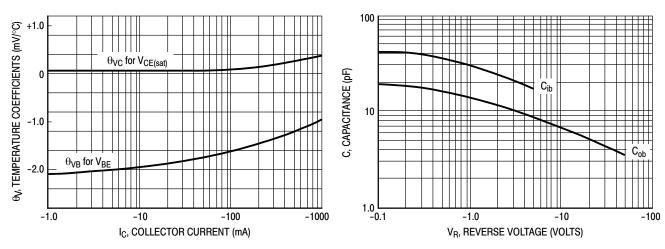


Figure 23. Temperature Coefficients

Figure 24. Capacitances

TYPICAL CHARACTERISTICS - BC807-16LT1, BC807-25LT1, BC807-40LT1

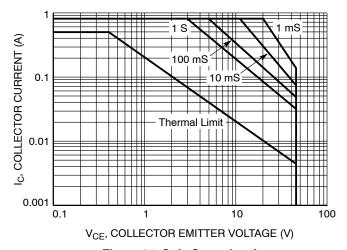


Figure 25. Safe Operating Area

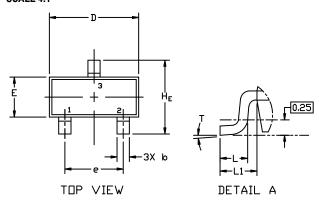


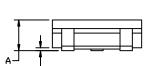


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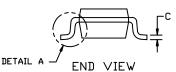
DATE 01 MAR 2023

SCALE 4:1





SIDE VIEW



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- CONTROLLING DIMENSION: MILLIMETERS
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIM	IETERS		INCHES		
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10°

GENERIC MARKING DIAGRAM*

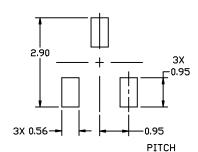


XXX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

STYLES ON PAGE 2

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SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	1	
STYLE 9:	STYLE 10:	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN		PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE		2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE		3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	I PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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